



ZXMN3A03E6

Product Summary

V _{(BR)DSS}	Max R _{DS(ON)}	Max I _D T _A = +25°C	
30V	$0.050\Omega @ V_{GS} = 10V$	4.6A	

Description and Applications

This new generation of TRENCH MOSFET from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

- DC DC converters
- Power Management Functions
- Disconnect Switches
- Motor Control

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

Case: SOT26

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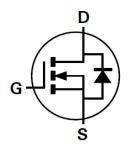
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.015 grams (Approximate)



SOT26

Top View





Device Symbol

Ordering Information (Note 4)

Part Number	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMN3A03E6TA	7	8	3000
ZXMN3A03E6TC	13	8	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

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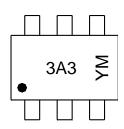
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2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



3A3 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Notes:

Dale Coue	Кеу												
Year	201	5 3	2016	2017	2018	2019	2020	202	1 20	22	2023	2024	2025
Code	С		D	E	F	G	Н	I		J	K	L	М
Mont	h	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GS}	±20	V
		T _A = +25°C (Note 6)	ID	4.6	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C$ (Note 6)		3.7	А
		T _A = +25°C (Note 5)		3.7	
Pulsed Drain Current (Note	7)	• • • •	I _{DM}	17	A
Continuous Source Current	(Body Diode) (N	lote 6)	Is	2.6	A
Pulsed Source Current (Bod	y Diode) (Note	7)	I _{SM}	17	A

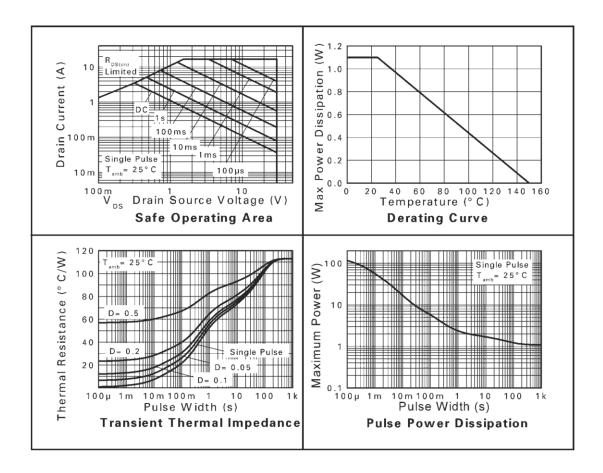
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear derating factor (Note 5)	PD	1.1 8.8	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ (Note 6) Linear derating factor (Note 6)	P _D	1.7 13.6	W mW/°C
Junction to Ambient (Note 5)	R _{0JA}	113	°C/W
Junction to Ambient (Note 6)	R _θ JA	73	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	۵°

Notes: 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. For a device surface mounted on FR-4 PCB measured at t≦10 secs.

7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width 10µs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

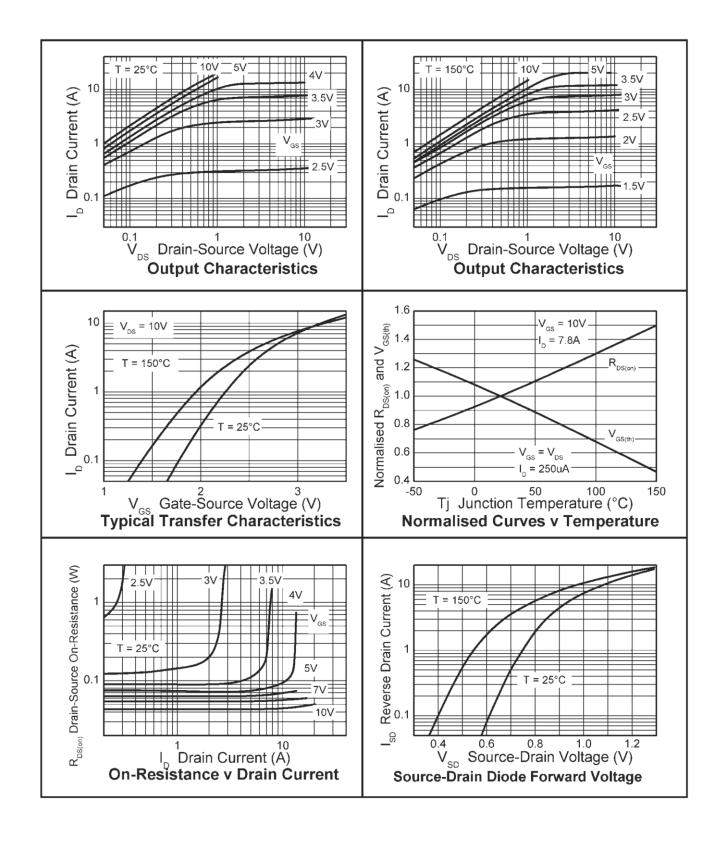
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-source Breakdown Voltage	BV _{DSS}	30	—	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	IDSS	_	_	0.5	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-body Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS						·	
Gate-source Threshold Voltage	V _{GS(th)}	1	_	—	V	$I_D = 250 \mu A$, $V_{DS} = V_{GS}$	
Statia Drain course On state Resistance (Note 8)	D			0.050	Ω	$V_{GS} = 10V, I_D = 7.8A$	
Static Drain-source On-state Resistance (Note 8)	R _{DS} (ON)	_	_	0.065	12	$V_{GS} = 4.5 V, I_D = 6.8 A$	
Forward Transconductance (Notes 8 & 10)	g fs	-	10	_	S	V _{DS} = 10V, I _D = 7.8A	
Diode Forward Voltage (Note 8)	V _{SD}	_	0.85	0.95	V	T _J = +25°C , I _S = 3.2A, V _{GS} = 0V	
DYNAMIC CHARACTERISTICS (Notes 9 & 10)						·	
Input Capacitance	Ciss		600	-	pF		
Output Capacitance		_	104	_	pF	−V _{DS} = 25V, V _{GS} = 0V −f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	-	58.5	_	pF		
Gate Charge	Qg	_	6.9	—	nC	V _{GS} = 5V, V _{DS} = 15V I _D = 3.5A	
Total Gate Charge	Qg		12.6	-	nC		
Gate-source Charge	Q _{gs}	_	2.0	—	nC	V _{GS} = 10V, V _{DS} = 15V - I _D = 3.5A	
Gate-drain Charge		_	2.0	_	nC	ID = 3.5A	
Reverse Recovery Time (Note 10)		_	18.8	_	ns	T _J = +25°C, I _F =3.5A,	
Reverse Recovery Charge (Note 10)	Q _{rr}	_	14.1	_	nC	di/dt= 100A/µs	
Turn-on Delay Time			2.9	—	ns		
Turn-on Rise Time			6.4	—	ns	V _{DD} = 15V, V _{GS} = 10V	
Turn-off Delay Time	t _{d(off)}	_	16.0	—	ns	$I_D = 3.5A, R_G = 6.0\Omega$	
Turn-off Fall Time	t _f		11.2	_	ns	7	

Notes:

8. Measured under pulsed conditions. Width=300µs. Duty cycle ≤ 2%.
9. Switching characteristics are independent of operating junction temperature.
10. For design aid only, not subject to production testing.

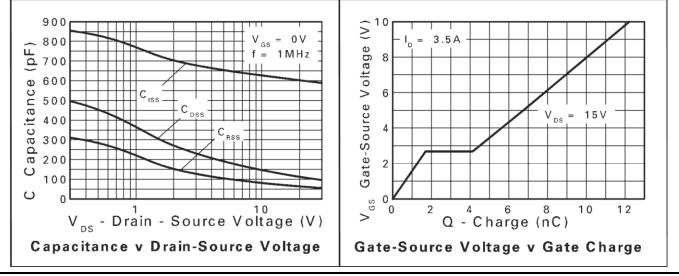


Typical Characteristics

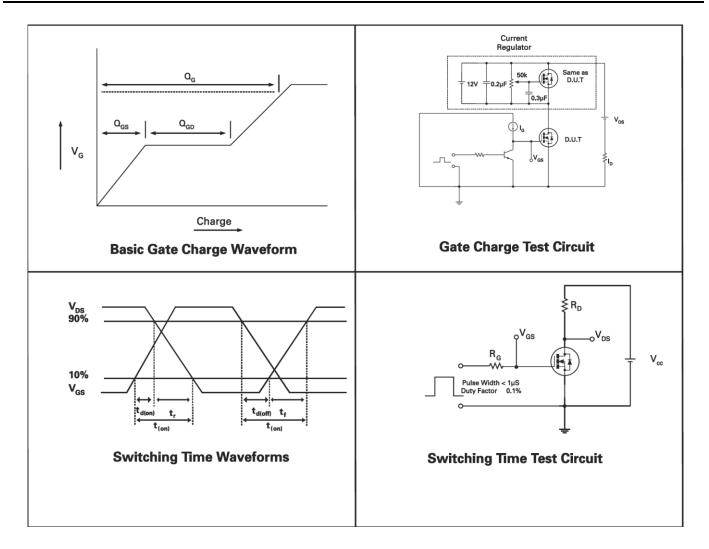




Typical Characteristics (Cont.)



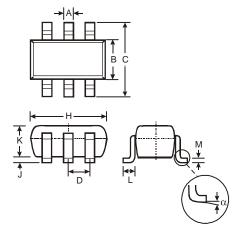
Test Circuits





Package Outline Dimensions

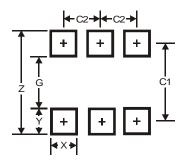
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26						
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D			0.95				
Н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
Κ	1.00	1.30	1.10				
L	0.35	0.55	0.40				
М	0.10	0.20	0.15				
α	0°	8°	—				
Ali D	imensi	ons in	mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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